

01-11-02

2872

985401/23401
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Vladimir Voronkov et al. Art Unit 2812
Serial No. 09/972,608
Filed October 5, 2001
Confirmation No. 4591
For METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON

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January 9, 2002

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,
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INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

The Commissioner is hereby authorized to charge any fees incurred regarding this Information Disclosure Statement to Account No. 19-1345 if an Office Action was issued prior to the date of mailing of this Statement.

Please note that Applicants make no representation as to the accuracy or completeness of the translations submitted herewith.

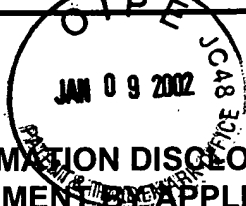
Respectfully submitted,

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				First Named Inventor	Vladimir Voronkov et al.
				Group Art Unit	2812
				Examiner Name	Unknown
Sheet	1	of	8	Attorney Docket No.	985401/23401

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	1	4,314,595		Yamamoto et al.	02/09/1982
	2	4,981,549		Yamashita et al.	01/01/1991
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	14	5,968,262		Saishouji et al.	10/19/1999

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	15	5,968,264		lida et al.	10/19/1999
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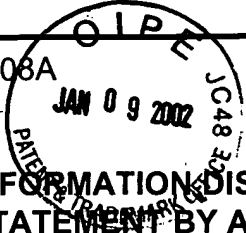
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
	22	EP	0 503 816	B1	Shin-Etsu Handotai Company Ltd.	09/16/1992	
	23	EP	0 504 837	A2	Shin-Etsu Handotai Company Ltd.	09/23/1992	
	24	EP	0 536 958	A1	Shin-Etsu Handotai Company Ltd.	04/14/1993	
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	27	EP	0 890 662	A1	Shinetsu Handotai KK	01/13/1999	
	28	EP	0 909 840	A1	Shinetsu Handota KK	04/21/1999	

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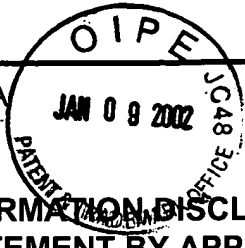
	29	EP	0 962 556	A1	Shin-Etsu Handotai Company Ltd.	12/08/1999	
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	46	PCT	WO 00/13211		MEMC Electronic Materials Inc.	03/09/2000	

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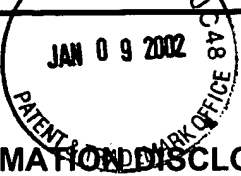
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	52	ABE, T., et al., "Behavior of Point Defects in FZ Silicon Crystals", Semiconductor Silicon 1990, <i>Proceedings of the Sixth International Symposium on Silicon Materials Science and Technology</i> , Vol. 90-7 (1990), pp. 105-116	
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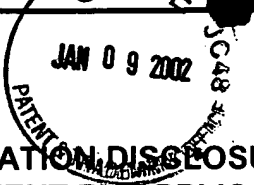
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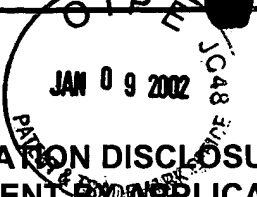
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PTO/SB/08A  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/972,608
				Filing Date	October 5, 2001
				Confirmation Number	4591
				First Named Inventor	Vladimir Voronkov et al.
				Group Art Unit	2812
				Examiner Name	Unknown
Sheet	8	of	8	Attorney Docket No.	985401/23401

	90	VORONKOV, V., et al., "Behaviour and Effects of Intrinsic Point Defects in the Growth of Large Silicon Crystals", Electrochemical Society proceedings, Volume 97-22, (8/1997), pp. 3-17	
	91	WIJARANAKULA, W., "Numerical Modeling of the Point Defect Aggregation during the Czochralski Silicon Crystal Growth", Journal of Electrochemical Society, Vol. 139, No. 2 (Feb. 1992), pp.604-616	
	92	WINKLER, R., et al. "Improvement of the Gate Oxide Integrity by Modifying Crystal Pulling and Its Impact on Device Failures" Journal of the Electrochemical Society, Vol. 141, No. 5 (5/1994) pp. 1398-1401.	
	93	ZIMMERMAN, H., et al. "Gold and Platinum Diffusion: the Key to the Understanding of Intrinsic Point Defect Behavior in Silicon", Applied Physics A Solids and Surfaces, Vol. A55, No. 1 (1992) pp. 121-134	
	94	ZIMMERMAN, H., et al. "Vacancy concentration wafer mapping in silicon" Journal of Crystal Growth, Vol. 129, (1993) pp. 582-592.	

Examiner Signature		Date Considered	
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